AMT1306

7 - 13GHz Multi-Function Chip



Key Features:

• Frequency range: 7 – 13GHz

• Receiver gain: 13dB

Transmitter small signal gain: 26dBReceiver output power P-1: 12dBm

• Transmitter saturated output power: 24dBm

Receiver noise figure: 8dBPhase shift bit: 6 bits

Phase shift step: 5.625°

Phase shift RMS: 2.5°, Phase shift additive attenuation ±1dB

Attenuation bit : 6 bitsAttenuation step : 0.5dB

• Attenuation RMS : 0.3dB, Attenuation additive phase shift $\pm 4^{\circ}$

Receiver Input/Output standing wave : 1.4
Transmitter Input/Output standing wave : 1.5

Operating voltage: +5V/+5V/-5V

• Static current: 80mA (transmitting) / 77mA (public) / 13mA (-5V)

Control method : TTL parallel control

• Chip dimensions: 4.5mm x 3.5mm x 0.1mm

• Applications: wireless communication, transceiver module, radio telecommunication etc.

Description:

AMT1306 is a multi-function chip incorporating with amplifier, switch, 6-digit attenuator, 6-digit phase shifter, control driver etc. X band MMIC, it uses Gallium Arsenide (GaAs) pHEMT process. The chip uses +5V/-5V operation voltage, control level is TTL, with parallel control for phase shift and attenuation. This chip is designed with ground through metal vias on the back technology. All chip products p are 100% RF tested.

Absolute Maximum Ratings (Ta = 25°C)

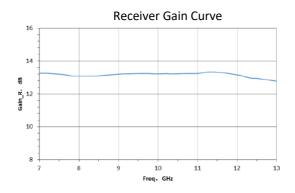
Symbol	Parameter	Value	Remark	
P1~P6, A1~A6, S1, S2	Control voltage	+6V		
VD1, VD2	Operating voltage	+6V		
VS	Operating voltage	-6V		
Pin	Input Power	+20dBm		
Tch	Operating Temperature	150°C		
Tm	Sintering Temperature	310°C	30s, N ₂ protection	
Tstg	Storage Temperature	-65 ~ +150°C		

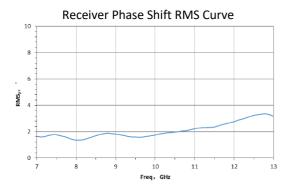
[1] Operation outside any of the Absolute Maximum Ratings may cause permanent device damage.

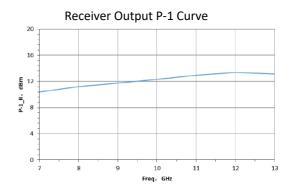
Electrical Characteristics (Ta = 25°C)

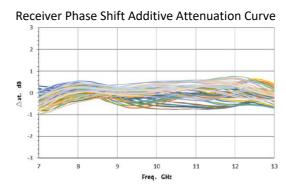
Symbol	Parameter	Value			Unit	Remark
		Min	Typical	Max		
F	Frequency	7~13		GHz		
Gain_R	Receiver gain	12.5	13	13.5	dB	
P-1_R	Receiver output at P-1 point	10	12	13	dBm	
NF_R	Noise figure	-	8	-	dB	
Gain_T	Transmitter small signal gain	24	26	30	dB	
Psat_T	Transmitter saturated output power - 24 -		dBm			
PS	Phase shift range	5.625 – 354.375 (6 bits phase shift)			0	
Δps	Phase shift additive attenuation variation	-1	-	+1	dB	
RMSps	Phase shift RMS	-	2.5	3.5	0	
ATT	Attenuation range	0.5 – 31.5 (6 bits attenuation)		dB		
∆at	Attenuation additive phase shift variation	-4 - +4		0		
RMS _{AT}	Attenuation RMS -		0.3	0.4	dB	
VSWR_R	Receiver Input/Output standing wave	-	1.4	-		
VSWR_T	Transmittter Input/Output standing wave	-	1.5	-		
ld2	+5V (transmitting) current	- 80 -		-	mA	
ld1	+5V (public) current	-	77	-	mA	
ls	-5V current	- 13 -		mA		

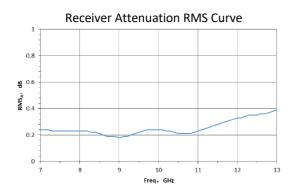
Typical Performance

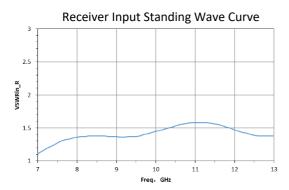


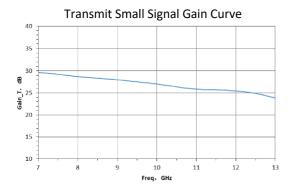


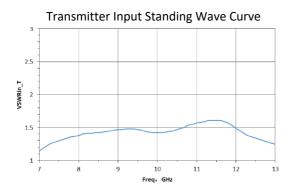


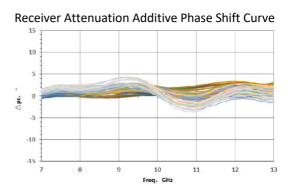


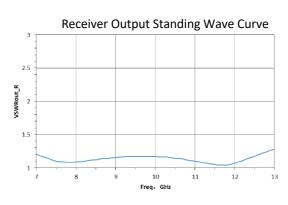


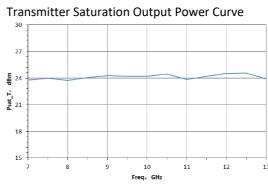


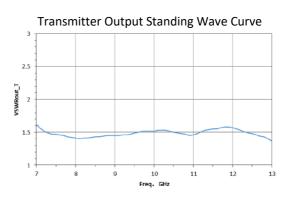




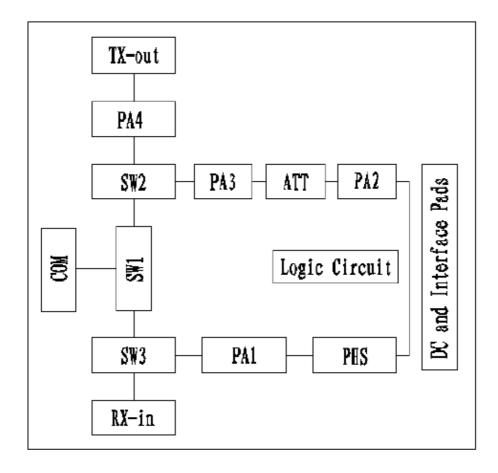




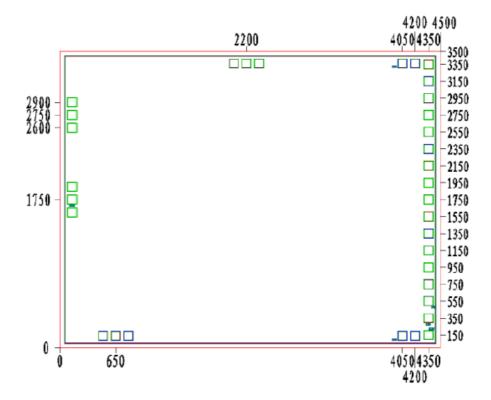




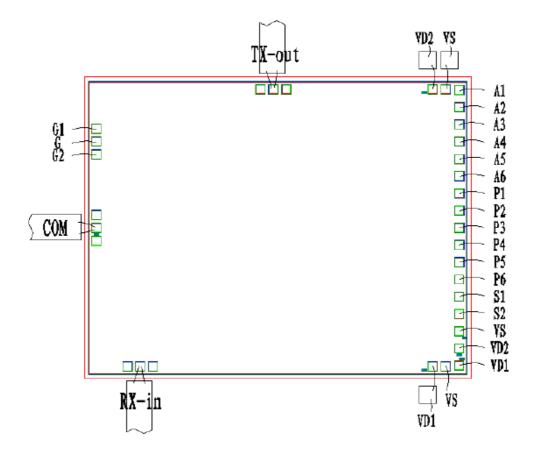
Internal Functional Block Diagram



Chip Dimensions (Unit : μm)



Chip Layout Diagram



Solder Pad Definition

Name	Dimension	Remark		
RX_in/TX_out	100μm x 100μm	Receiver Input/Transmitter Output, receiver input port needs to connect to ground		
COM	100μm x 100μm	Receiver Output/Transmitter Input		
VD1 / VD2 / VDS	100μm x 100μm	Supply pad : +5V(public)/+5V(transmit)/-5V		
A1~A6, P1~P6	100μm x 100μm	TTL, attenuation phase shift control signal		
S1, S2	100μm x 100μm	TTL, switch control signal		
G1, G2	100μm x 100μm	1dB, 2dB gain adjust		

Phase Shift Attenuation Truth Table

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Phase Shift	5.625°	11.25°	22.5°	45°	90°	180°	
Initial	0	0	0	0	0	0	
-5.625°	1	0	0	0	0	0	
-11.25°	0	1	0	0	0	0	
-22.5°	0	0	1	0	0	0	
-45°	0	0	0	1	0	0	
-90°	0	0	0	0	1	0	
-180°	0	0	0	0	0	1	
Attenuation	0.5dB	1dB	2dB	4dB	8dB	16dB	
Initial	0	0	0	0	0	0	
0.5dB	1	0	0	0	0	0	
1dB	0	1	0	0	0	0	
2dB	0	0	1	0	0	0	
4dB	0	0	0	1	0	0	
8dB	0	0	0	0	1	0	
16dB	0	0	0	0	0	1	

Switch Truth Table

S1	S2	COM-TX_out	COM-RX_in	COM_Load
1	0	On	Off	Off
0	1	Off	On	Off
0	0	Off	Off	On
1	1	On	Off	Off

Please see Appendix A for details.